

AMENDMENTS TO THE SPECIFICATION:

Please amend the specification as follows:

The paragraph starting at line 10 on page 31 is amended as follows:

Furthermore, the dielectric constants of the respective insulating films are formed so as to differ from each other. Namely, the silicon oxide film ~~[[32]]~~ 31 which is an insulating material whose dielectric constant is low is formed so as to be filled in the groove 18A. Therefore, a data interference effect due to the capacitive coupling between the floating electrodes FG which are adjacent along the control electrodes CG can be suppressed to a minimum. Here, the data interference effect due to the capacitive coupling between the floating electrodes FG means the effect in which the threshold voltages of the adjacent floating electrodes FG are affected in accordance with the electrical states of the floating electrodes FG. For example, it means that the threshold voltages of the adjacent floating electrodes FG are affected in accordance with whether electrons are injected in the floating electrodes FG or not. Accordingly, when the effect is large, the ability to control ~~[[of]]~~ the threshold voltages of the respective nonvolatile memory elements MC deteriorates. However, the silicon oxide film ~~[[32]]~~ 31 which is an insulating material whose dielectric constant is low is filled in the groove 18A. Therefore, the electrical effect between the adjacent floating electrodes FG can be suppressed to a minimum. As a result, the above-described data interference effect can be suppressed to a minimum, and the reliabilities of the respective nonvolatile memory elements MC can be improved.